

Ting-Chang Chang

List of Publications by Year
in descending order

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512
papers

9,808
citations

50276
46
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79698
73
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516
all docs

516
docs citations

516
times ranked

5446
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 1 | Resistance random access memory. Materials Today, 2016, 19, 254-264. | 14.2 | 391 |
| 2 | Developments in nanocrystal memory. Materials Today, 2011, 14, 608-615. | 14.2 | 285 |
| 3 | Influence of electrode material on the resistive memory switching property of indium gallium zinc oxide thin films. Applied Physics Letters, 2010, 96, . | 3.3 | 188 |
| 4 | Behaviors of InGaZnO thin film transistor under illuminated positive gate-bias stress. Applied Physics Letters, 2010, 97, . | 3.3 | 166 |
| 5 | Influence of positive bias stress on N2O plasma improved InGaZnO thin film transistor. Applied Physics Letters, 2010, 96, . | 3.3 | 158 |
| 6 | Multilevel resistive switching in Ti/CuxO/Pt memory devices. Journal of Applied Physics, 2010, 108, . | 2.5 | 144 |
| 7 | Investigating the degradation behavior caused by charge trapping effect under DC and AC gate-bias stress for InGaZnO thin film transistor. Applied Physics Letters, 2011, 99, . | 3.3 | 135 |
| 8 | Physical and chemical mechanisms in oxide-based resistance random access memory. Nanoscale Research Letters, 2015, 10, 120. | 5.7 | 130 |
| 9 | Bias-induced oxygen adsorption in zinc tin oxide thin film transistors under dynamic stress. Applied Physics Letters, 2010, 96, . | 3.3 | 120 |
| 10 | Redox Reaction Switching Mechanism in RRAM Device With $\text{Pt/CoSiO}_2/\text{TiN}$ Structure. IEEE Electron Device Letters, 2011, 32, 545-547. | 3.9 | 120 |
| 11 | High-Performance Visible-Blind Ultraviolet Photodetector Based on IGZO TFT Coupled with p-n Heterojunction. ACS Applied Materials & Interfaces, 2018, 10, 8102-8109. | 8.0 | 106 |
| 12 | Bipolar Resistive Switching Characteristics of Transparent Indium Gallium Zinc Oxide Resistive Random Access Memory. Electrochemical and Solid-State Letters, 2010, 13, H191. | 2.2 | 100 |
| 13 | Atomic-level quantized reaction of HfO_x memristor. Applied Physics Letters, 2013, 102, 172903. | 3.3 | 100 |
| 14 | Integrated One Diode–One Resistor Architecture in Nanopillar SiO_x Resistive Switching Memory by Nanosphere Lithography. Nano Letters, 2014, 14, 813-818. | 9.1 | 97 |
| 15 | Light-induced instability of an InGaZnO thin film transistor with and without SiO _x passivation layer formed by plasma-enhanced-chemical-vapor-deposition. Applied Physics Letters, 2010, 97, . | 3.3 | 95 |
| 16 | Functionally Complete Boolean Logic in 1T1R Resistive Random Access Memory. IEEE Electron Device Letters, 2017, 38, 179-182. | 3.9 | 95 |
| 17 | Demonstration of Synaptic Behaviors and Resistive Switching Characterizations by Proton Exchange Reactions in Silicon Oxide. Scientific Reports, 2016, 6, 21268. | 3.3 | 84 |
| 18 | A low-temperature method for improving the performance of sputter-deposited ZnO thin-film transistors with supercritical fluid. Applied Physics Letters, 2009, 94, . | 3.3 | 72 |

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 19 | Environment-dependent thermal instability of sol-gel derived amorphous indium-gallium-zinc-oxide thin film transistors. Applied Physics Letters, 2011, 98, 152109. | 3.3 | 72 |
| 20 | An electro-photo-sensitive synaptic transistor for edge neuromorphic visual systems. Nanoscale, 2019, 11, 17590-17599. | 5.6 | 71 |
| 21 | Effects of Ambient Atmosphere on Electrical Characteristics of Al ₂ O ₃ Passivated InGaZnO Thin Film Transistors during Positive-Bias-Temperature-Stress Operation. Electrochemical and Solid-State Letters, 2011, 14, H177. | 2.2 | 70 |
| 22 | Low-power bipolar resistive switching TiN/HfO ₂ /ITO memory with self-compliance current phenomenon. Applied Physics Express, 2014, 7, 034101. | 2.4 | 70 |
| 23 | Enhancing the Oxygen Plasma Resistance of Low-kMethylsilsesquioxane by H ₂ Plasma Treatment. Japanese Journal of Applied Physics, 1999, 38, 3482-3486. | 1.5 | 65 |
| 24 | Influence of H ₂ O Dipole on Subthreshold Swing of Amorphous Indium-Gallium-Zinc-Oxide Thin Film Transistors. Electrochemical and Solid-State Letters, 2011, 14, H114. | 2.2 | 64 |
| 25 | Characteristics and Mechanisms of Silicon-Oxide-Based Resistance Random Access Memory. IEEE Electron Device Letters, 2013, 34, 399-401. | 3.9 | 62 |
| 26 | Efficient Implementation of Boolean and Full-Adder Functions With 1T1R RRAMs for Beyond Von Neumann In-Memory Computing. IEEE Transactions on Electron Devices, 2018, 65, 4659-4666. | 3.0 | 57 |
| 27 | Realization of Functional Complete Stateful Boolean Logic in Memristive Crossbar. ACS Applied Materials & Interfaces, 2016, 8, 34559-34567. | 8.0 | 56 |
| 28 | Attaining resistive switching characteristics and selector properties by varying forming polarities in a single HfO ₂ -based RRAM device with a vanadium electrode. Nanoscale, 2017, 9, 8586-8590. | 5.6 | 56 |
| 29 | Origin of Hopping Conduction in Graphene-Oxide-Doped Silicon Oxide Resistance Random Access Memory Devices. IEEE Electron Device Letters, 2013, 34, 677-679. | 3.9 | 55 |
| 30 | Charge Quantity Influence on Resistance Switching Characteristic During Forming Process. IEEE Electron Device Letters, 2013, 34, 502-504. | 3.9 | 55 |
| 31 | Characterization of Oxygen Accumulation in Indium-Tin-Oxide for Resistance Random Access Memory. IEEE Electron Device Letters, 2014, 35, 630-632. | 3.9 | 55 |
| 32 | Nonvolatile reconfigurable sequential logic in a HfO ₂ resistive random access memory array. Nanoscale, 2017, 9, 6649-6657. | 5.6 | 55 |
| 33 | A Novel Nanowire Channel Poly-Si TFT Functioning as Transistor and Nonvolatile SONOS Memory. IEEE Electron Device Letters, 2007, 28, 809-811. | 3.9 | 54 |
| 34 | Conduction Mechanism and Improved Endurance in HfO ₂ -Based RRAM with Nitridation Treatment. Nanoscale Research Letters, 2017, 12, 574. | 5.7 | 54 |
| 35 | Functional Demonstration of a Memristive Arithmetic Logic Unit (MemALU) for In-Memory Computing. Advanced Functional Materials, 2019, 29, 1905660. | 14.9 | 54 |
| 36 | Reducing operation current of Ni-doped silicon oxide resistance random access memory by supercritical CO ₂ fluid treatment. Applied Physics Letters, 2011, 99, . | 3.3 | 53 |

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|----|---|------|-----------|
| 37 | High-Density Memristor-CMOS Ternary Logic Family. IEEE Transactions on Circuits and Systems I: Regular Papers, 2021, 68, 264-274. | 5.4 | 53 |
| 38 | A study of resistive switching effects on a thin FeOx transition layer produced at the oxide/iron interface of TiN/SiO ₂ /Fe-contented electrode structures. Applied Physics Letters, 2010, 96, 052111. | 3.3 | 51 |
| 39 | Influence of Nanocrystals on Resistive Switching Characteristic in Binary Metal Oxides Memory Devices. Electrochemical and Solid-State Letters, 2011, 14, H135. | 2.2 | 51 |
| 40 | Effects of H ₂ plasma treatment on low dielectric constant methylsilsesquioxane. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2325. | 1.6 | 50 |
| 41 | Bulk Oxygen Ion Storage in Indium Tin Oxide Electrode for Improved Performance of HfO ₂ -Based Resistive Random Access Memory. IEEE Electron Device Letters, 2016, 37, 280-283. | 3.9 | 50 |
| 42 | Flexible low-temperature polycrystalline silicon thin-film transistors. Materials Today Advances, 2020, 5, 100040. | 5.2 | 50 |
| 43 | Strategies to Improve the Accuracy of Memristor-Based Convolutional Neural Networks. IEEE Transactions on Electron Devices, 2020, 67, 895-901. | 3.0 | 49 |
| 44 | High-performance hydrogenated amorphous-Si TFT for AMLCD and AMOLED applications. IEEE Electron Device Letters, 2005, 26, 731-733. | 3.9 | 48 |
| 45 | The Effect of Silicon Oxide Based RRAM with Tin Doping. Electrochemical and Solid-State Letters, 2012, 15, H65. | 2.2 | 48 |
| 46 | Bipolar Resistive RAM Characteristics Induced by Nickel Incorporated Into Silicon Oxide Dielectrics for IC Applications. IEEE Electron Device Letters, 2012, 33, 1696-1698. | 3.9 | 48 |
| 47 | LiSiO _x -Based Analog Memristive Synapse for Neuromorphic Computing. IEEE Electron Device Letters, 2019, 40, 542-545. | 3.9 | 48 |
| 48 | Impact of repeated uniaxial mechanical strain on p-type flexible polycrystalline thin film transistors. Applied Physics Letters, 2015, 106, . | 3.3 | 47 |
| 49 | Effect of mechanical-strain-induced defect generation on the performance of flexible amorphous InGaZnO thin-film transistors. Applied Physics Express, 2016, 9, 124101. | 2.4 | 47 |
| 50 | Reconfigurable Boolean Logic in Memristive Crossbar: The Principle and Implementation. IEEE Electron Device Letters, 2019, 40, 200-203. | 3.9 | 47 |
| 51 | Low operation voltage macromolecular composite memory assisted by graphene nanoflakes. Journal of Materials Chemistry C, 2013, 1, 552-559. | 5.5 | 46 |
| 52 | Adaptive Synaptic Memory via Lithium Ion Modulation in RRAM Devices. Small, 2020, 16, e2003964. | 10.0 | 46 |
| 53 | Origin of Hopping Conduction in Sn-Doped Silicon Oxide RRAM With Supercritical CO ₂ Fluid Treatment. IEEE Electron Device Letters, 2012, 33, 1693-1695. | 3.9 | 45 |
| 54 | Complementary resistive switching behavior induced by varying forming current compliance in resistance random access memory. Applied Physics Letters, 2015, 106, . | 3.3 | 45 |

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| 55 | Characteristics of hafnium oxide resistance random access memory with different setting compliance current. Applied Physics Letters, 2013, 103, . | 3.3 | 44 |
| 56 | Enhancement of Brightness Uniformity by a New Voltage-Modulated Pixel Design for AMOLED Displays. IEEE Electron Device Letters, 2006, 27, 743-745. | 3.9 | 43 |
| 57 | Resistive switching characteristics of Sm ₂ O ₃ thin films for nonvolatile memory applications. Solid-State Electronics, 2011, 63, 189-191. | 1.4 | 43 |
| 58 | Investigating the Drain-Bias-Induced Degradation Behavior Under Light Illumination for InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2012, 33, 1000-1002. | 3.9 | 43 |
| 59 | Hopping effect of hydrogen-doped silicon oxide insert RRAM by supercritical CO ₂ fluid treatment. IEEE Electron Device Letters, 2013, 34, 617-619. | 3.9 | 42 |
| 60 | Effects of Repetitive Mechanical Bending Strain on Various Dimensions of Foldable Low Temperature Polysilicon TFTs Fabricated on Polyimide. IEEE Electron Device Letters, 2016, 37, 1010-1013. | 3.9 | 42 |
| 61 | Performance and characteristics of double layer porous silicon oxide resistance random access memory. Applied Physics Letters, 2013, 102, . | 3.3 | 41 |
| 62 | Resistance Switching Induced by Hydrogen and Oxygen in Diamond-Like Carbon Memristor. IEEE Electron Device Letters, 2014, 35, 1016-1018. | 3.9 | 41 |
| 63 | Dual Ion Effect of the Lithium Silicate Resistance Random Access Memory. IEEE Electron Device Letters, 2014, 35, 530-532. | 3.9 | 41 |
| 64 | Analog Resistive Switching and Synaptic Functions in WO _x /TaO _x Bilayer through Redox-Induced Trap-Controlled Conduction. ACS Applied Electronic Materials, 2019, 1, 2422-2430. | 4.3 | 41 |
| 65 | NBTI Degradation in LTPS TFTs Under Mechanical Tensile Strain. IEEE Electron Device Letters, 2011, 32, 907-909. | 3.9 | 40 |
| 66 | Investigation for coexistence of dual resistive switching characteristics in DyMn ₂ O ₅ memory devices. Applied Physics Letters, 2011, 99, . | 3.3 | 40 |
| 67 | Self-Heating-Effect-Induced Degradation Behaviors in a-InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2013, 34, 63-65. | 3.9 | 40 |
| 68 | Endurance Improvement Technology With Nitrogen Implanted in the Interface of WSiO_x Resistance Switching Device. IEEE Electron Device Letters, 2013, 34, 864-866. | 3.9 | 40 |
| 69 | Review of Present Reliability Challenges in Amorphous In-Ga-Zn-O Thin Film Transistors. ECS Journal of Solid State Science and Technology, 2014, 3, Q3058-Q3070. | 1.8 | 40 |
| 70 | Surface Engineering of Polycrystalline Silicon for Long-Term Mechanical Stress Endurance Enhancement in Flexible Low-Temperature Poly-Si Thin-Film Transistors. ACS Applied Materials & Interfaces, 2017, 9, 11942-11949. | 8.0 | 40 |
| 71 | Reliability characteristics of NiSi nanocrystals embedded in oxide and nitride layers for nonvolatile memory application. Applied Physics Letters, 2008, 92, 152114. | 3.3 | 39 |
| 72 | Silicon introduced effect on resistive switching characteristics of WOX thin films. Applied Physics Letters, 2012, 100, 022904. | 3.3 | 39 |

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|----|--|-----|-----------|
| 73 | Electrical conduction mechanism of Zn:SiO _x resistance random access memory with supercritical CO ₂ fluid process. Applied Physics Letters, 2013, 103, 083509. | 3.3 | 39 |
| 74 | Resistive Switching Modification by Ultraviolet Illumination in Transparent Electrode Resistive Random Access Memory. IEEE Electron Device Letters, 2014, 35, 633-635. | 3.9 | 39 |
| 75 | Suppress temperature instability of InGaZnO thin film transistors by N ₂ O plasma treatment, including thermal-induced hole trapping phenomenon under gate bias stress. Applied Physics Letters, 2012, 100, . | 3.3 | 38 |
| 76 | Effects of Varied Negative Stop Voltages on Current Self-Compliance in Indium Tin Oxide Resistance Random Access Memory. IEEE Electron Device Letters, 2015, 36, 564-566. | 3.9 | 37 |
| 77 | Low-temperature method for enhancing sputter-deposited HfO ₂ films with complete oxidization. Applied Physics Letters, 2007, 91, 012109. | 3.3 | 36 |
| 78 | Self-heating enhanced charge trapping effect for InGaZnO thin film transistor. Applied Physics Letters, 2012, 101, 042101. | 3.3 | 35 |
| 79 | Dehydroxyl effect of Sn-doped silicon oxide resistance random access memory with supercritical CO ₂ fluid treatment. Applied Physics Letters, 2012, 101, . | 3.3 | 35 |
| 80 | Improvement of resistance switching characteristics in a thin FeOx transition layer of TiN/SiO ₂ /FeOx/FePt structure by rapid annealing. Applied Physics Letters, 2010, 96, 222108. | 3.3 | 34 |
| 81 | Bipolar resistive switching of chromium oxide for resistive random access memory. Solid-State Electronics, 2011, 62, 40-43. | 1.4 | 34 |
| 82 | Resistive switching characteristics of gallium oxide for nonvolatile memory application. Thin Solid Films, 2013, 529, 200-204. | 1.8 | 34 |
| 83 | A New Pixel Circuit Compensating for Brightness Variation in Large Size and High Resolution AMOLED Displays. Journal of Display Technology, 2007, 3, 398-403. | 1.2 | 33 |
| 84 | Temperature and frequency dependence of the ferroelectric characteristics of BaTiO ₃ thin films for nonvolatile memory applications. Applied Physics A: Materials Science and Processing, 2007, 89, 533-536. | 2.3 | 33 |
| 85 | Hot carrier effect on gate-induced drain leakage current in high-k/metal gate n-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2011, 99, . | 3.3 | 33 |
| 86 | Investigation statistics of bipolar multilevel memristive mechanism and characterizations in a thin FeOx transition layer of TiN/SiO ₂ /FeOx/Fe structure. Journal of Applied Physics, 2011, 110, . | 2.5 | 33 |
| 87 | Asymmetric Carrier Conduction Mechanism by Tip Electric Field in WSiO_2 Resistance Switching Device. IEEE Electron Device Letters, 2012, 33, 342-344. | 3.9 | 33 |
| 88 | High-performance polycrystalline silicon thin-film transistor with multiple nanowire channels and lightly doped drain structure. Applied Physics Letters, 2004, 84, 3822-3824. | 3.3 | 32 |
| 89 | The effect of high/low permittivity in bilayer HfO ₂ /BN resistance random access memory. Applied Physics Letters, 2013, 102, . | 3.3 | 32 |
| 90 | Temperature-Dependent Instability of Bias Stress in InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2014, 61, 2119-2124. | 3.0 | 32 |

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| 91 | Dynamic conductance characteristics in HfO _x -based resistive random access memory. RSC Advances, 2017, 7, 12984-12989. | 3.6 | 32 |
| 92 | Investigation of on-current degradation behavior induced by surface hydrolysis effect under negative gate bias stress in amorphous InGaZnO thin-film transistors. Applied Physics Letters, 2014, 104, . | 3.3 | 31 |
| 93 | Galvanic Effect of Au–Ag Electrodes for Conductive Bridging Resistive Switching Memory. IEEE Electron Device Letters, 2015, 36, 1321-1324. | 3.9 | 31 |
| 94 | Resistive Switching Mechanism of Oxygen-Rich Indium Tin Oxide Resistance Random Access Memory. IEEE Electron Device Letters, 2016, 37, 408-411. | 3.9 | 31 |
| 95 | High-Precision Symmetric Weight Update of Memristor by Gate Voltage Ramping Method for Convolutional Neural Network Accelerator. IEEE Electron Device Letters, 2020, 41, 353-356. | 3.9 | 31 |
| 96 | Improved memory window for Ge nanocrystals embedded in SiON layer. Applied Physics Letters, 2006, 89, 162105. | 3.3 | 30 |
| 97 | Low Temperature Improvement Method on $\text{m Zn}_{\text{x}}\text{SiO}_{\text{x}}$ Resistive Random Access Memory Devices. IEEE Electron Device Letters, 2013, 34, 511-513. | 3.9 | 30 |
| 98 | Rational Hydrogenation for Enhanced Mobility and High Reliability on ZnO-based Thin Film Transistors: From Simulation to Experiment. ACS Applied Materials & Interfaces, 2016, 8, 5408-5415. | 8.0 | 30 |
| 99 | Influence of Oxygen Concentration on Resistance Switching Characteristics of Gallium Oxide. IEEE Electron Device Letters, 2012, 33, 1387-1389. | 3.9 | 29 |
| 100 | Hot-Carrier Effect on Amorphous In-Ga-Zn-O Thin-Film Transistors With a Via-Contact Structure. IEEE Electron Device Letters, 2013, 34, 638-640. | 3.9 | 29 |
| 101 | A Method to Reduce Forming Voltage Without Degrading Device Performance in Hafnium Oxide-Based 1T1R Resistive Random Access Memory. IEEE Journal of the Electron Devices Society, 2018, 6, 341-345. | 2.1 | 29 |
| 102 | Influence of Bias-Induced Copper Diffusion on the Resistive Switching Characteristics of a SiON Thin Film. Electrochemical and Solid-State Letters, 2011, 14, H93. | 2.2 | 28 |
| 103 | Origin of self-heating effect induced asymmetrical degradation behavior in InGaZnO thin-film transistors. Applied Physics Letters, 2012, 100, 232101. | 3.3 | 28 |
| 104 | Solution-based I^2 -diketonate silver ink for direct printing of highly conductive features on a flexible substrate. Journal of Materials Chemistry C, 2013, 1, 5161. | 5.5 | 28 |
| 105 | Improving Performance by Doping Gadolinium Into the Indium-Tin–Oxide Electrode in HfO ₂ -Based Resistive Random Access Memory. IEEE Electron Device Letters, 2016, 37, 584-587. | 3.9 | 28 |
| 106 | Investigation of channel width-dependent threshold voltage variation in a-InGaZnO thin-film transistors. Applied Physics Letters, 2014, 104, . | 3.3 | 27 |
| 107 | Hydrogen induced redox mechanism in amorphous carbon resistive random access memory. Nanoscale Research Letters, 2014, 9, 52. | 5.7 | 27 |
| 108 | Resistance Switching Characteristics Induced by O ₂ Plasma Treatment of an Indium Tin Oxide Film for Use as an Insulator in Resistive Random Access Memory. ACS Applied Materials & Interfaces, 2017, 9, 3149-3155. | 8.0 | 27 |

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| 109 | Enhanced electrical behavior from the galvanic effect in Ag-Cu alloy electrode conductive bridging resistive switching memory. Applied Physics Letters, 2018, 113, . | 3.3 | 27 |
| 110 | Ultra-violet light enhanced super critical fluid treatment in In-Ga-Zn-O thin film transistor. Applied Physics Letters, 2014, 104, . | 3.3 | 26 |
| 111 | The Demonstration of Increased Selectivity During Experimental Measurement in Filament-Type Vanadium Oxide-Based Selector. IEEE Transactions on Electron Devices, 2018, 65, 4622-4627. | 3.0 | 26 |
| 112 | Solution-processed amorphous Ga ₂ O ₃ :CdO TFT-type deep-UV photodetectors. Applied Physics Letters, 2020, 116, . | 3.3 | 26 |
| 113 | High temperature-induced abnormal suppression of sub-threshold swing and on-current degradations under hot-carrier stress in a-InGaZnO thin film transistors. Applied Physics Letters, 2013, 103, . | 3.3 | 25 |
| 114 | Improvement of Resistive Switching Characteristic in Silicon Oxide-Based RRAM Through Hydride-Oxidation on Indium Tin Oxide Electrode by Supercritical CO ₂ Fluid. IEEE Electron Device Letters, 2015, 36, 558-560. | 3.9 | 25 |
| 115 | Hydrogen Diffusion and Threshold Voltage Shifts in Top-Gate Amorphous InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2020, 67, 3123-3128. | 3.0 | 25 |
| 116 | A low temperature fabrication of HfO ₂ films with supercritical CO ₂ fluid treatment. Journal of Applied Physics, 2008, 103, . | 2.5 | 24 |
| 117 | Systematic Investigations on Self-Heating-Effect-Induced Degradation Behavior in a-InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2012, 59, 3389-3395. | 3.0 | 24 |
| 118 | Ultra-high resistive switching mechanism induced by oxygen ion accumulation on nitrogen-doped resistive random access memory. Applied Physics Letters, 2014, 105, . | 3.3 | 24 |
| 119 | Effects of Channel Width on Electrical Characteristics of Polysilicon TFTs With Multiple Nanowire Channels. IEEE Transactions on Electron Devices, 2005, 52, 2343-2346. | 3.0 | 23 |
| 120 | Low-Temperature Passivation of Amorphous-Silicon Thin-Film Transistors With Supercritical Fluids. IEEE Electron Device Letters, 2007, 28, 584-586. | 3.9 | 23 |
| 121 | On the Origin of Hole Valence Band Injection on GIFBE in PD SOI n-MOSFETs. IEEE Electron Device Letters, 2010, 31, 540-542. | 3.9 | 23 |
| 122 | Tri-Resistive Switching Behavior of Hydrogen Induced Resistance Random Access Memory. IEEE Electron Device Letters, 2014, 35, 217-219. | 3.9 | 23 |
| 123 | Role of H ₂ O Molecules in Passivation Layer of a-InGaZnO Thin Film Transistors. IEEE Electron Device Letters, 2017, 38, 469-472. | 3.9 | 23 |
| 124 | H ₂ O adsorption on amorphous In-Ga-Zn-O thin-film transistors under negative bias stress. Applied Physics Letters, 2017, 111, . | 3.3 | 23 |
| 125 | Analysis of Negative Bias Temperature Instability Degradation in p-Type Low-Temperature Polycrystalline Silicon Thin-Film Transistors of Different Grain Sizes. IEEE Electron Device Letters, 2019, 40, 1768-1771. | 3.9 | 23 |
| 126 | Surface states related the bias stability of amorphous In _{0.5} Ga _{0.5} Zn _{0.5} O thin film transistors under different ambient gasses. Thin Solid Films, 2011, 520, 1432-1436. | 1.8 | 22 |

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| 127 | Impact of static and dynamic stress on threshold voltage instability in high-k/metal gate n-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2011, 98, . | 3.3 | 22 |
| 128 | Application of in-cell touch sensor using photo-leakage current in dual gate a-InGaZnO thin-film transistors. Applied Physics Letters, 2012, 101, . | 3.3 | 22 |
| 129 | Engineering interface-type resistance switching based on forming current compliance in ITO/Ga ₂ O ₃ :ITO/TiN resistance random access memory: Conduction mechanisms, temperature effects, and electrode influence. Applied Physics Letters, 2016, 109, . | 3.3 | 21 |
| 130 | Research on Temperature Effect in Insulator“Metal Transition Selector Based on NbO _x Thin Films. IEEE Transactions on Electron Devices, 2018, 65, 5448-5452. | 3.0 | 21 |
| 131 | Drain-Induced-Barrier-Lowering-Like Effect Induced by Oxygen-Vacancy in Scaling-Down via-Contact Type Amorphous InGaZnO Thin-Film Transistors. IEEE Journal of the Electron Devices Society, 2018, 6, 685-690. | 2.1 | 21 |
| 132 | Investigation of the Capacitance“Voltage Electrical Characteristics of Thin-Film Transistors Caused by Hydrogen Diffusion under Negative Bias Stress in a Moist Environment. ACS Applied Materials & Interfaces, 2019, 11, 40196-40203. | 8.0 | 21 |
| 133 | Gate Modulation of Excitatory and Inhibitory Synaptic Plasticity in a Low-Temperature Polysilicon Thin Film Synaptic Transistor. ACS Applied Electronic Materials, 2019, 1, 132-140. | 4.3 | 21 |
| 134 | Physical and electrical characteristics of Ba(Zr _{0.1} Ti _{0.9})O ₃ thin films under oxygen plasma treatment for applications in nonvolatile memory devices. Applied Physics A: Materials Science and Processing, 2007, 90, 329-331. | 2.3 | 20 |
| 135 | Low temperature improvement method on characteristics of Ba(Zr _{0.1} Ti _{0.9})O ₃ thin films deposited on indium tin oxide/glass substrates. Applied Physics A: Materials Science and Processing, 2010, 99, 291-295. | 2.3 | 20 |
| 136 | Investigating the improvement of resistive switching trends after post-forming negative bias stress treatment. Applied Physics Letters, 2011, 99, 132104. | 3.3 | 20 |
| 137 | Carrier Transport and Multilevel Switching Mechanism for Chromium Oxide Resistive Random-Access Memory. Electrochemical and Solid-State Letters, 2011, 14, H103. | 2.2 | 20 |
| 138 | High-stability oxygen sensor based on amorphous zinc tin oxide thin film transistor. Applied Physics Letters, 2012, 100, . | 3.3 | 20 |
| 139 | Hopping conduction distance dependent activation energy characteristics of Zn:SiO ₂ resistance random access memory devices. Applied Physics Letters, 2013, 102, . | 3.3 | 20 |
| 140 | Investigation of a Hump Phenomenon in Back-Channel-Etched Amorphous In-Ga-Zn-O Thin-Film Transistors Under Negative Bias Stress. IEEE Electron Device Letters, 2017, 38, 592-595. | 3.9 | 20 |
| 141 | Model of dielectric breakdown in hafnia-based ferroelectric capacitors. Journal of Applied Physics, 2018, 124, . | 2.5 | 20 |
| 142 | Nonvolatile memory characteristics of nickel-silicon-nitride nanocrystal. Applied Physics Letters, 2007, 91, 082103. | 3.3 | 19 |
| 143 | Charge storage characteristics of Mo nanocrystal dependence on Mo oxide reduction. Applied Physics Letters, 2008, 93, 222101. | 3.3 | 19 |
| 144 | Mechanism of Triple Ions Effect in GeSO Resistance Random Access Memory. IEEE Electron Device Letters, 2015, 36, 552-554. | 3.9 | 19 |

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| 145 | Effects of plasma treatment time on surface characteristics of indium-tin-oxide film for resistive switching storage applications. <i>Applied Surface Science</i> , 2017, 414, 224-229. | 6.1 | 19 |
| 146 | Solving the Scaling Issue of Increasing Forming Voltage in Resistive Random Access Memory Using High- κ Spacer Structure. <i>Advanced Electronic Materials</i> , 2017, 3, 1700171. | 5.1 | 19 |
| 147 | High-Voltage Backside-Illuminated CMOS Photovoltaic Module for Powering Implantable Temperature Sensors. <i>IEEE Journal of Photovoltaics</i> , 2018, 8, 342-347. | 2.5 | 19 |
| 148 | Reducing Forming Voltage by Applying Bipolar Incremental Step Pulse Programming in a 1T1R Structure Resistance Random Access Memory. <i>IEEE Electron Device Letters</i> , 2018, 39, 815-818. | 3.9 | 19 |
| 149 | Reconfigurable logic in nanosecond Cu/GeTe/TiN filamentary memristors for energy-efficient in-memory computing. <i>Nanotechnology</i> , 2018, 29, 385203. | 2.6 | 19 |
| 150 | Broadband Optoelectronic Synaptic Thin-Film Transistors Based on Oxide Semiconductors. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020, 14, 1900630. | 2.4 | 19 |
| 151 | Improvement of Resistive Switching Characteristics in Zinc Oxide-Based Resistive Random Access Memory by Ammoniation Annealing. <i>IEEE Electron Device Letters</i> , 2020, 41, 357-360. | 3.9 | 19 |
| 152 | Fabrication of One-Transistor-Capacitor Structure of Nonvolatile TFT Ferroelectric RAM Devices Using $\text{Ba}(\text{Zr}_{0.1}\text{Ti}_{0.9})\text{O}_3$ Gated Oxide Film. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2007, 54, 1726-1730. | 3.0 | 18 |
| 153 | On the Origin of Gate-Induced Floating-Body Effect in PD SOI p-MOSFETs. <i>IEEE Electron Device Letters</i> , 2011, 32, 847-849. | 3.9 | 18 |
| 154 | H ₂ O-Assisted O ₂ Adsorption in Sol-Gel Derived Amorphous Indium Gallium Zinc Oxide Thin Film Transistors. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, H235. | 2.2 | 18 |
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